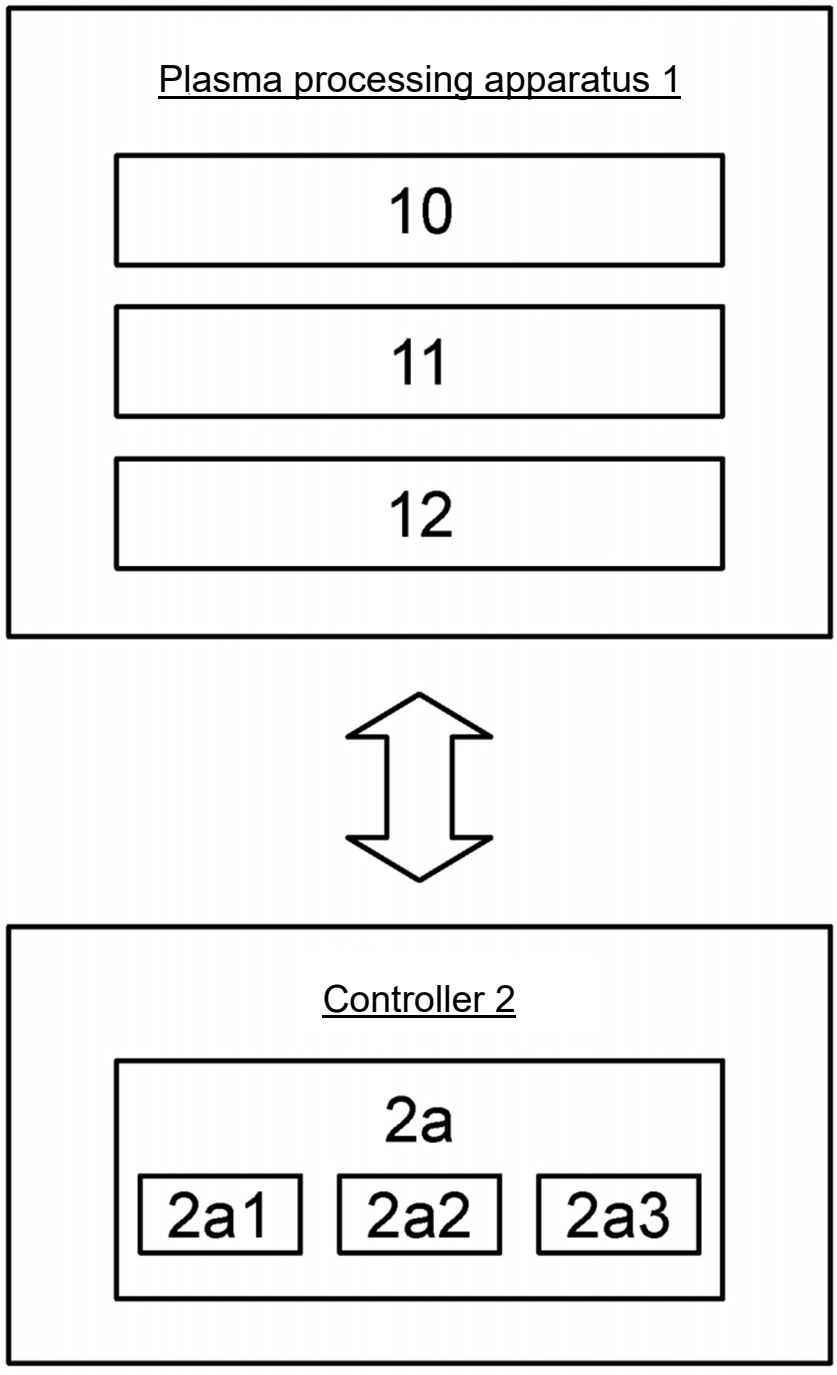
FIG. 1


Plasma processing apparatus 1
10
11
12
Controller 2
2a
2a1
2a2
2a3

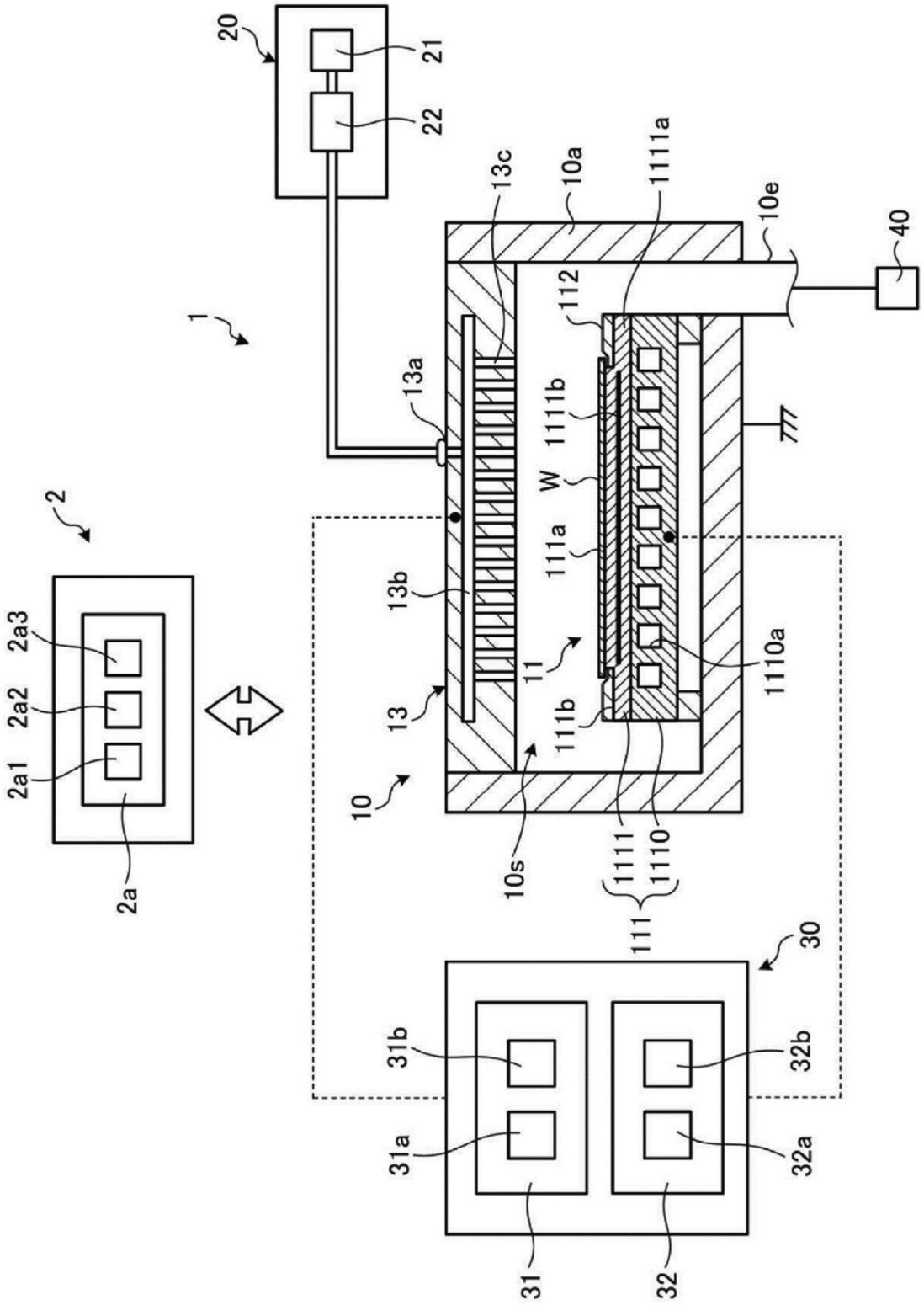

20
21
22
1
2
2a3
2a2
2a1
2a
13c
10a
1111a
10e
40
112
13a
1111b
W
111a
13b
11
13
111b
1110a
10
10s
1111
1110
111
30
31b
32b
31a
32a
31
32

FIG. 2

FIG. 3

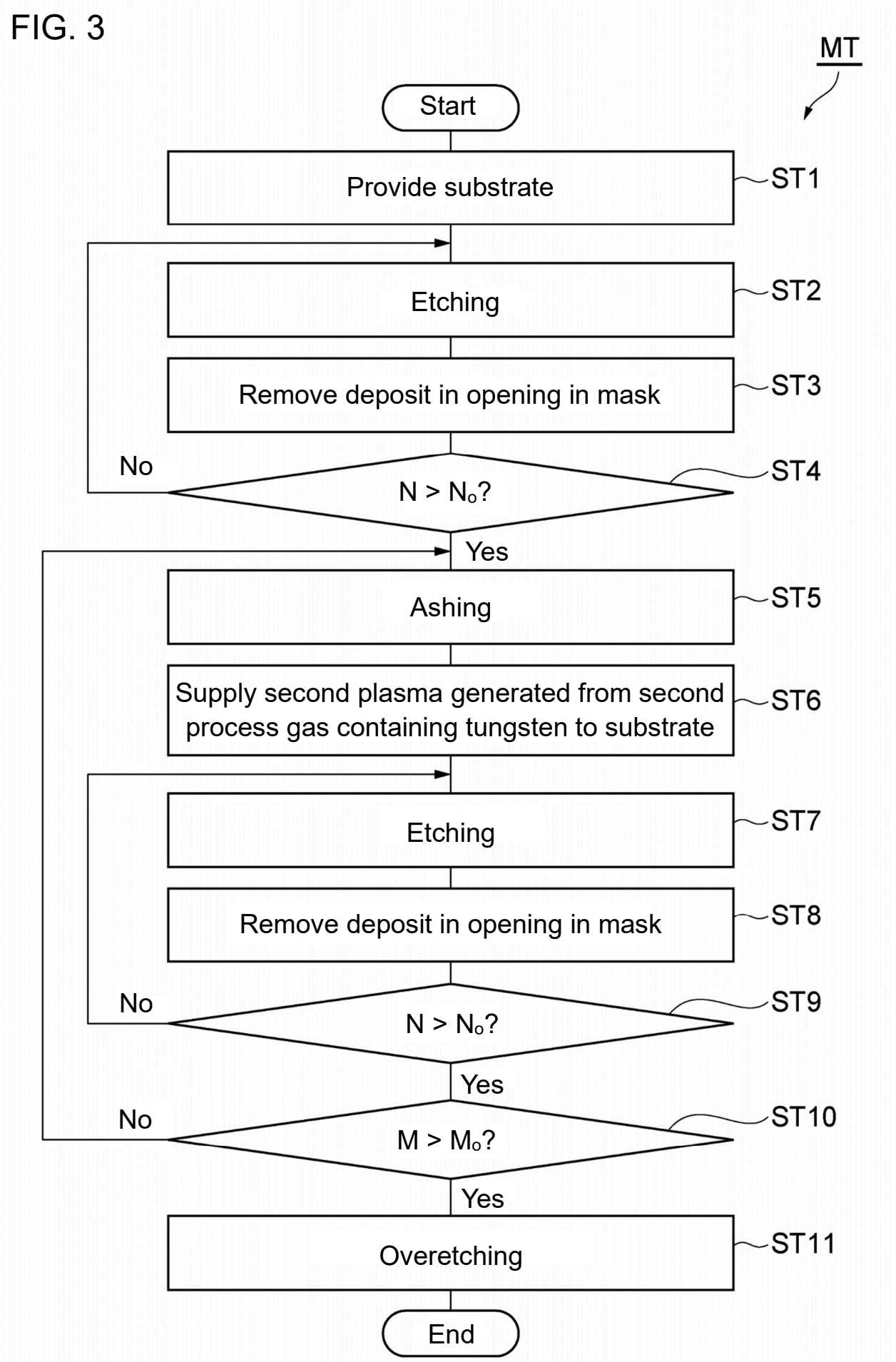

MT
Start
Provide substrate
ST1
Etching
ST2
Remove deposit in opening in mask
ST3
No
N > No?
ST4
Yes
Ashing
ST5
Supply second plasma generated from second process gas containing tungsten to substrate
ST6
Etching
ST7
Remove deposit in opening in mask
ST8
No
N > No?
ST9
Yes
No
M > Mo?
ST10
Yes
Overetching
ST11
End

FIG. 4

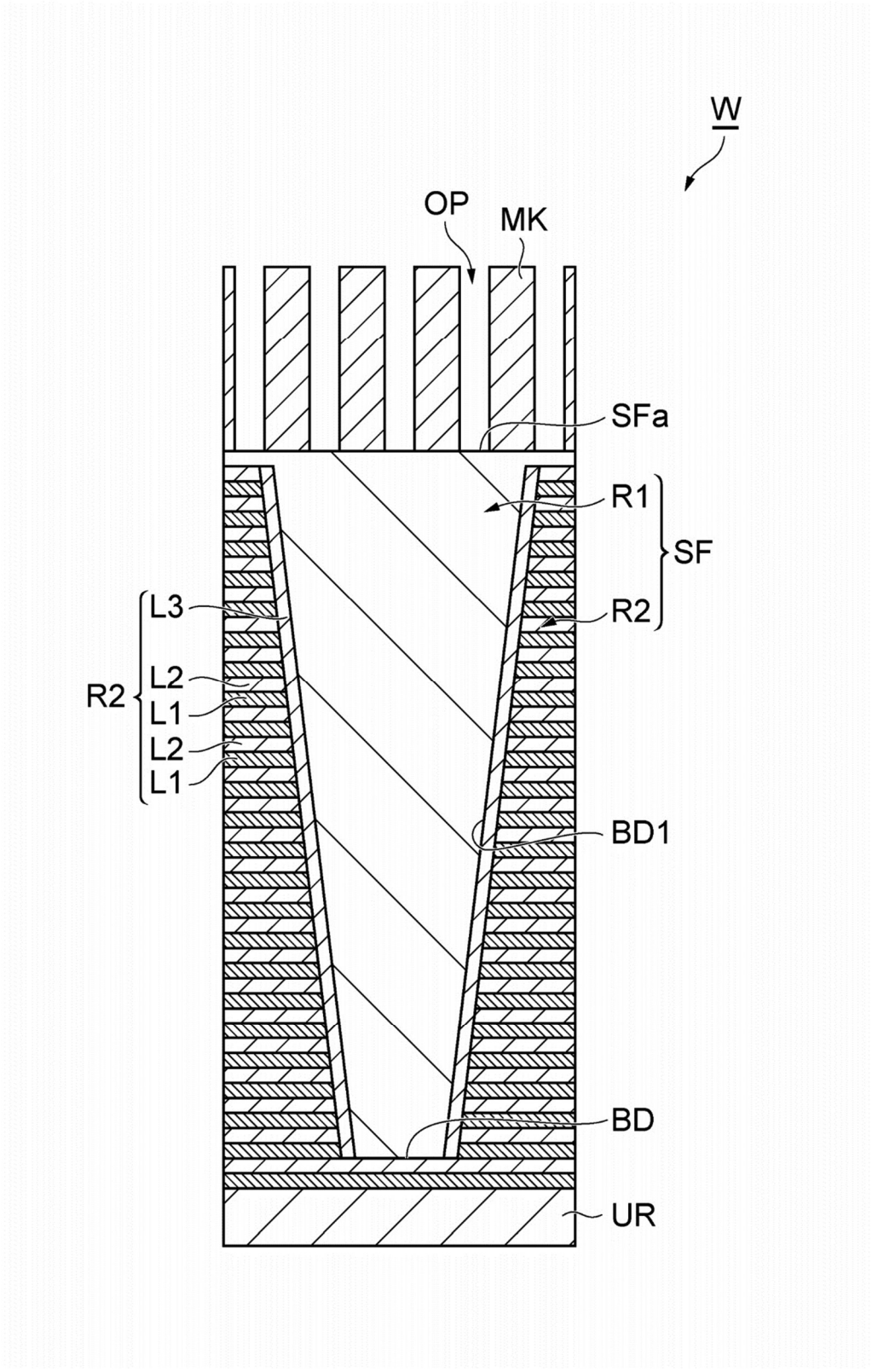


FIG. 5

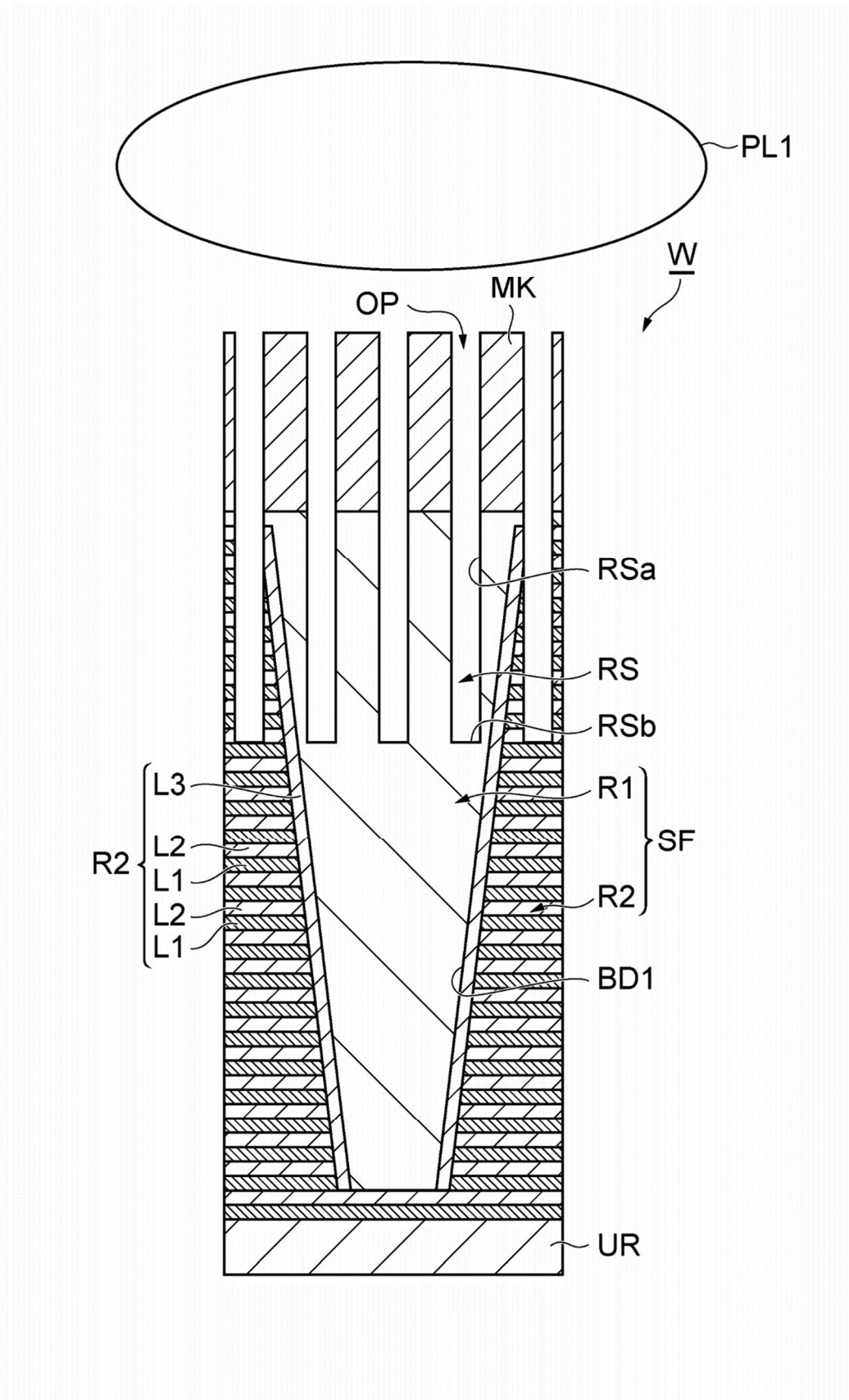


FIG. 6

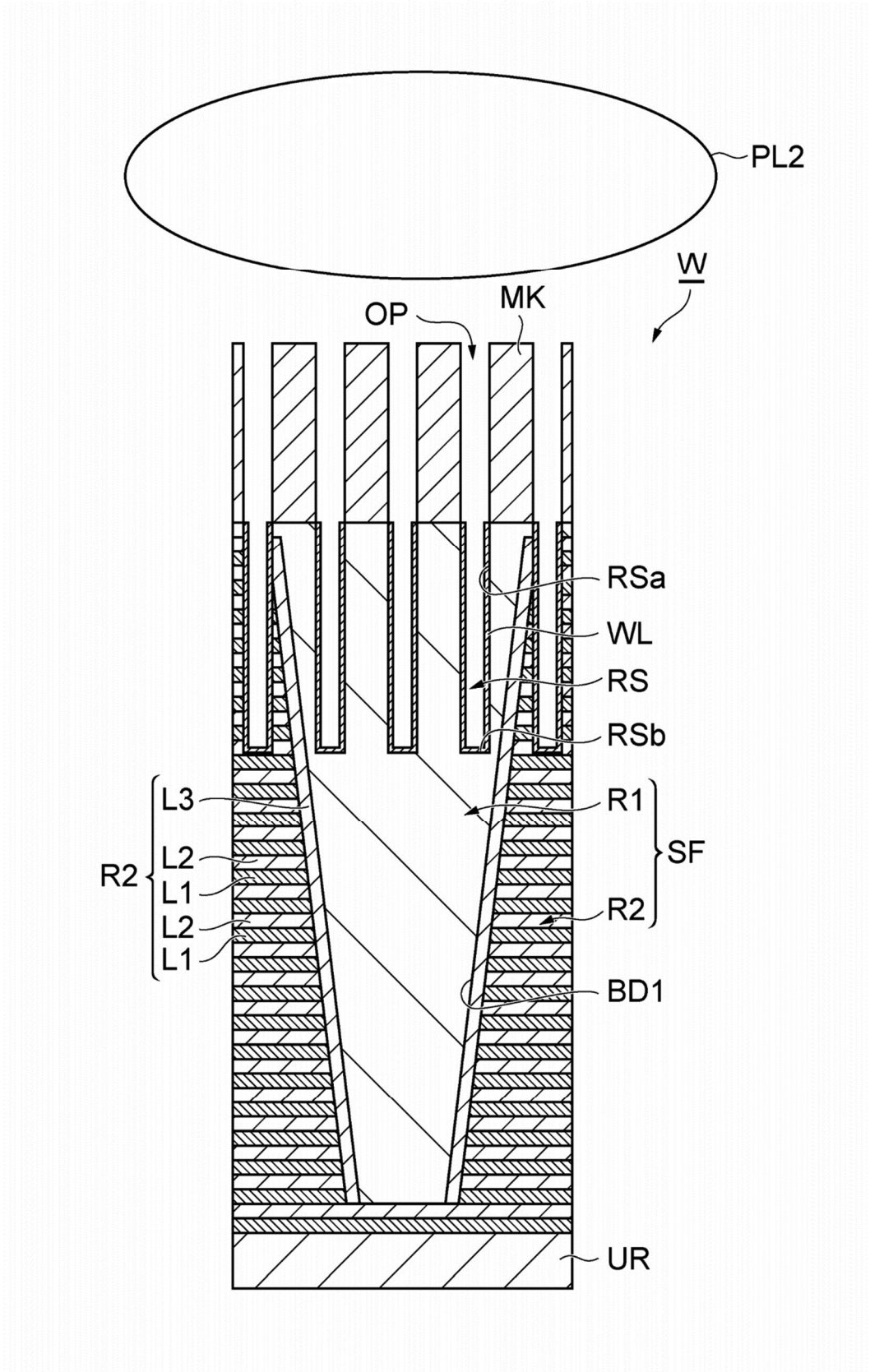


FIG. 7

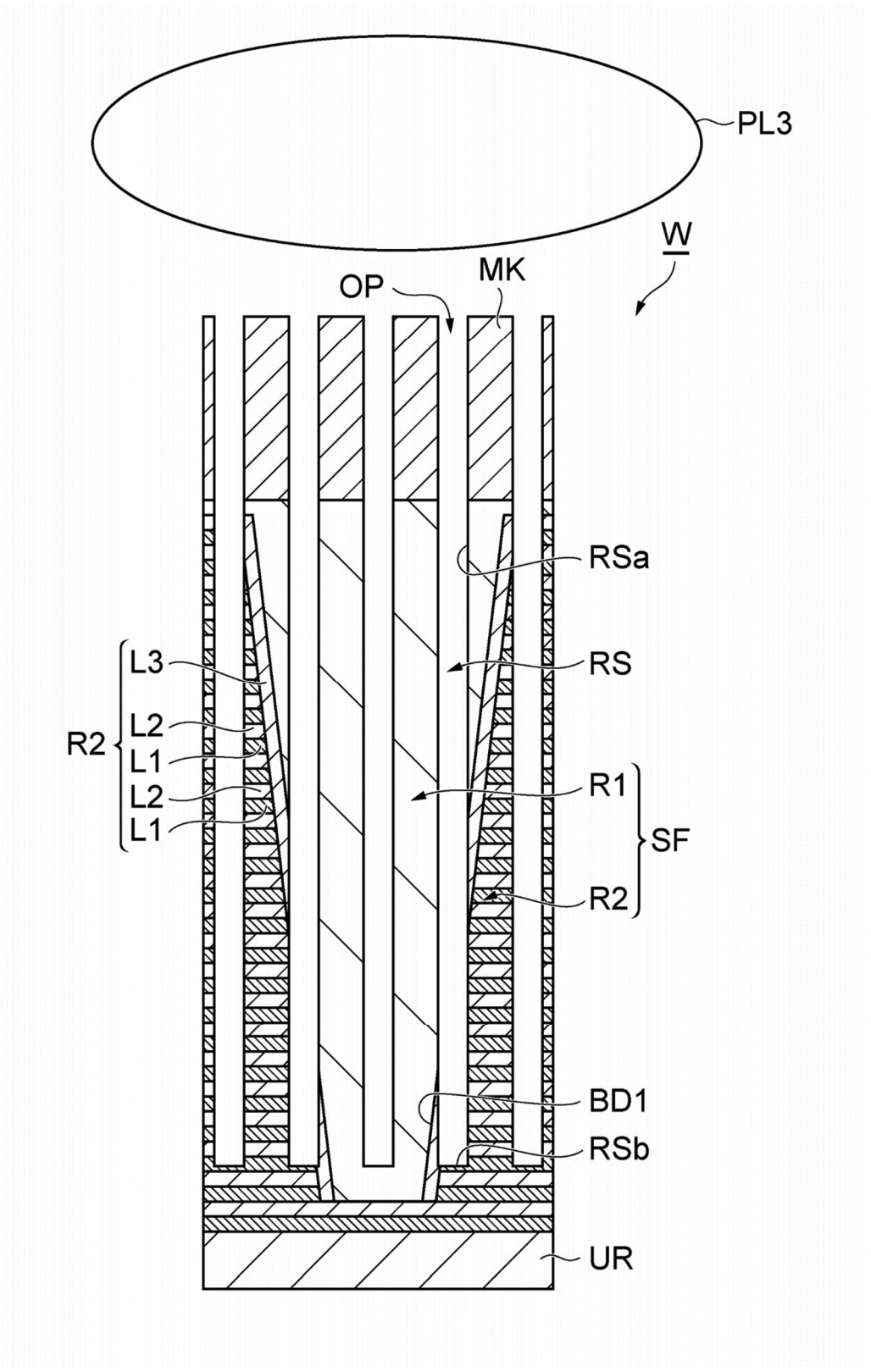


FIG. 8

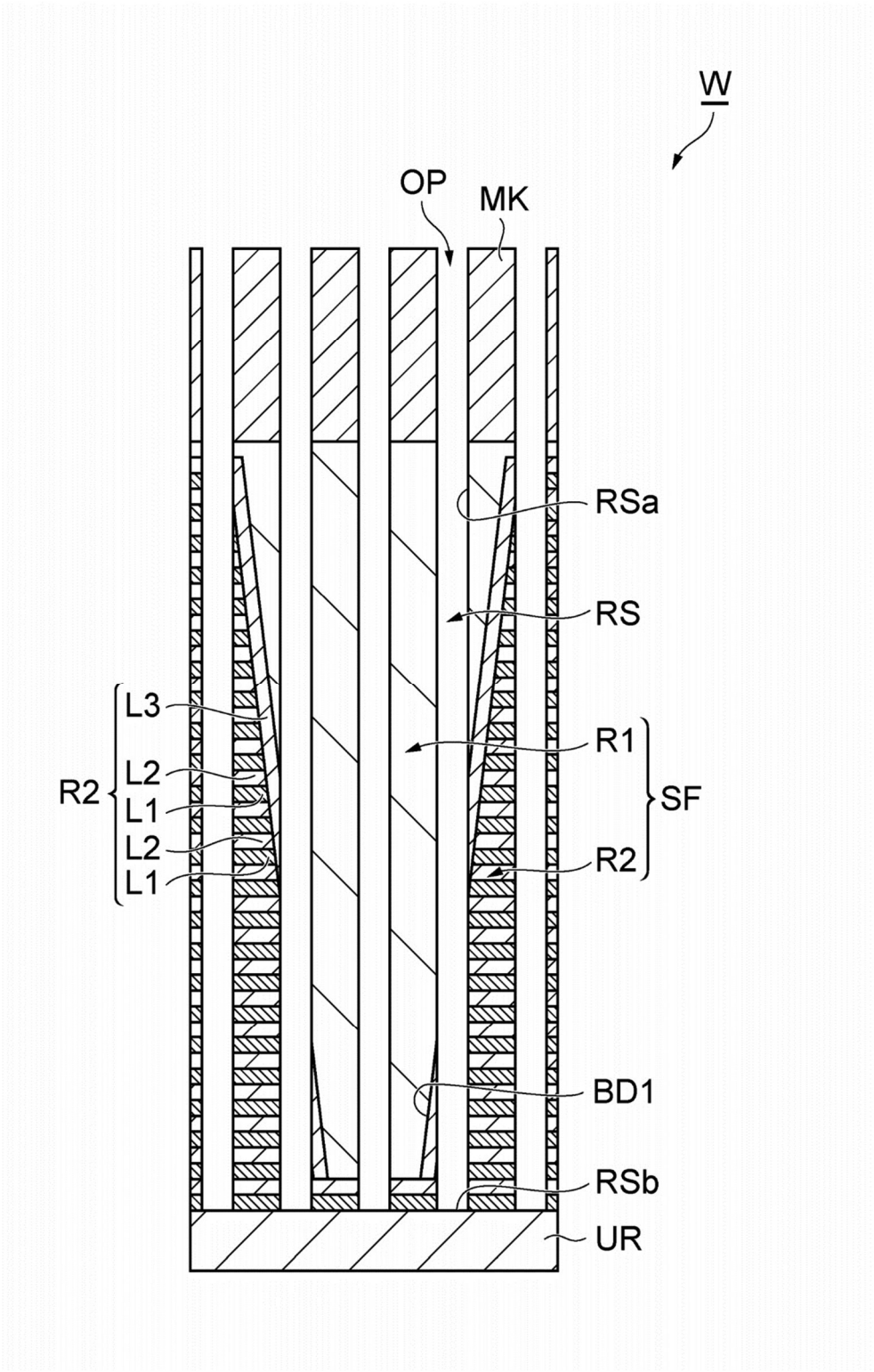


FIG. 9

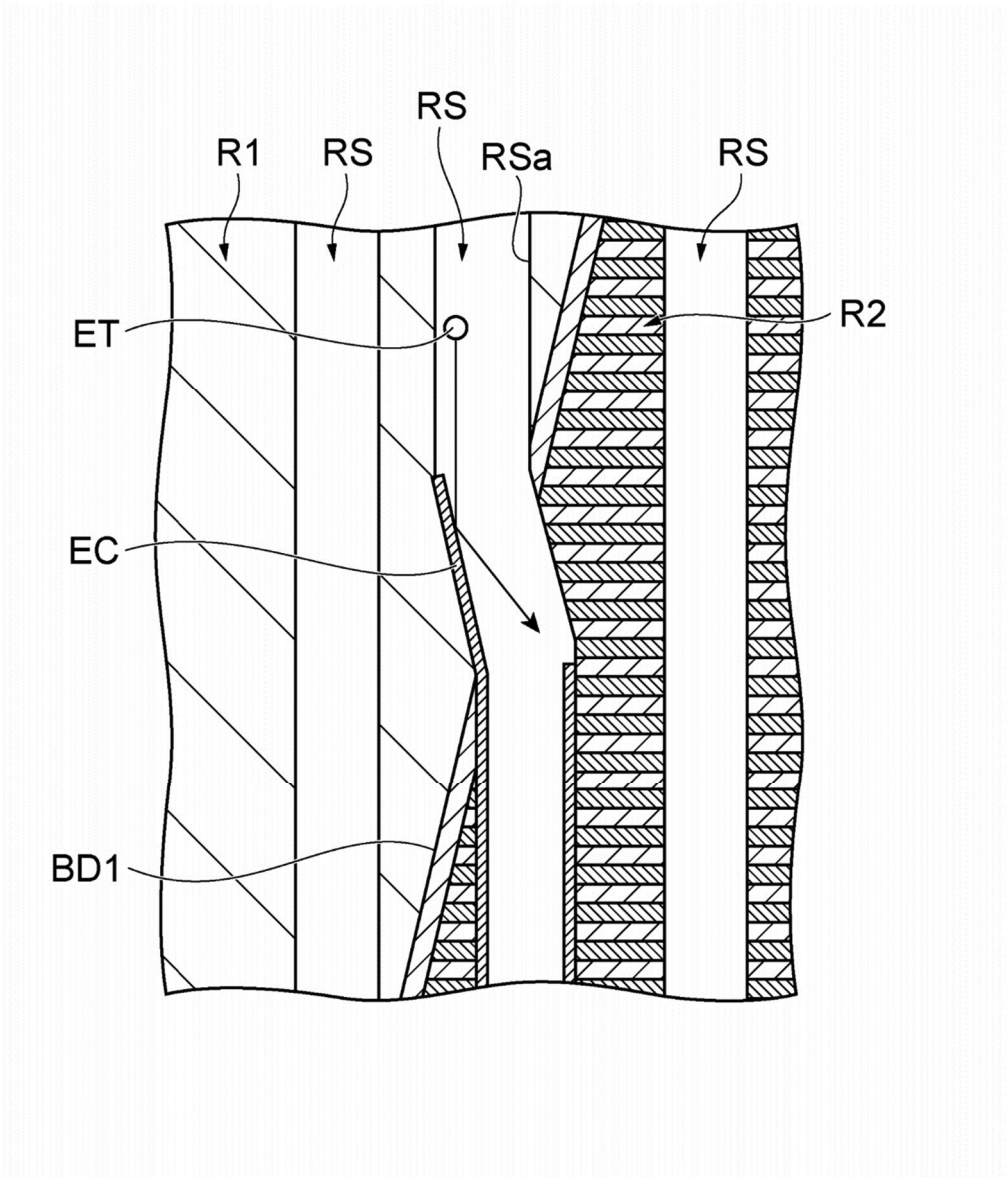
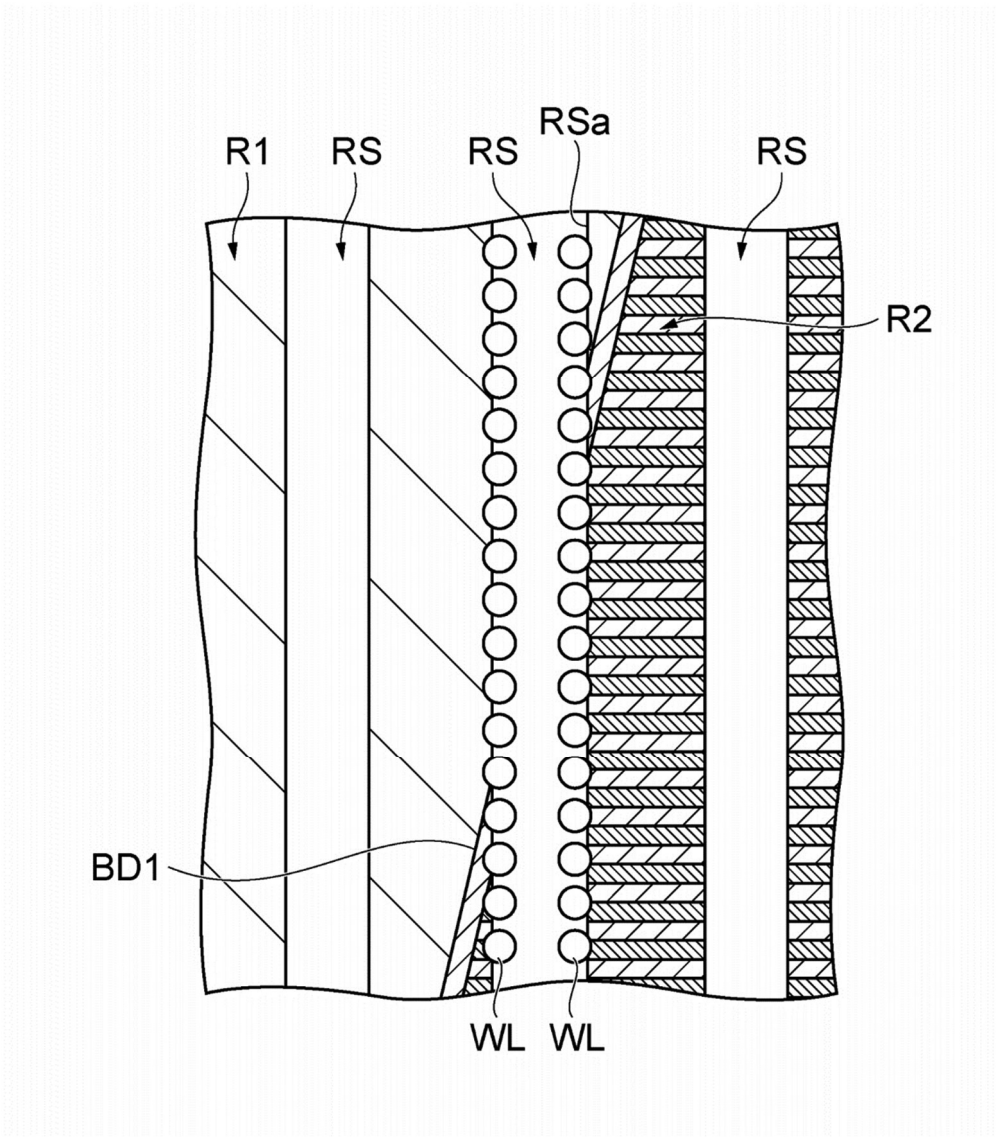


FIG. 10



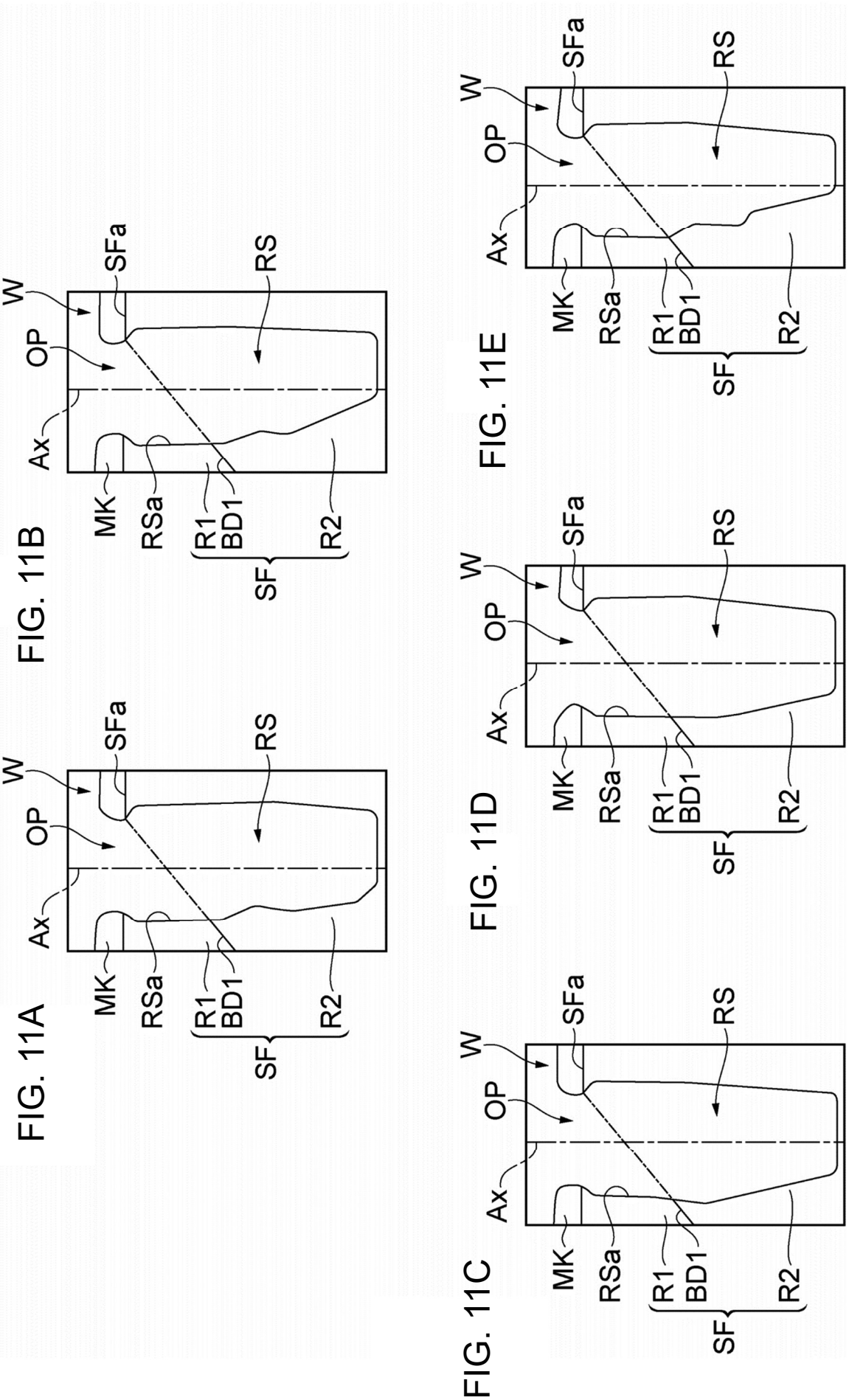


FIG. 11A

FIG. 11B

FIG. 11C

FIG. 11D

FIG. 11E

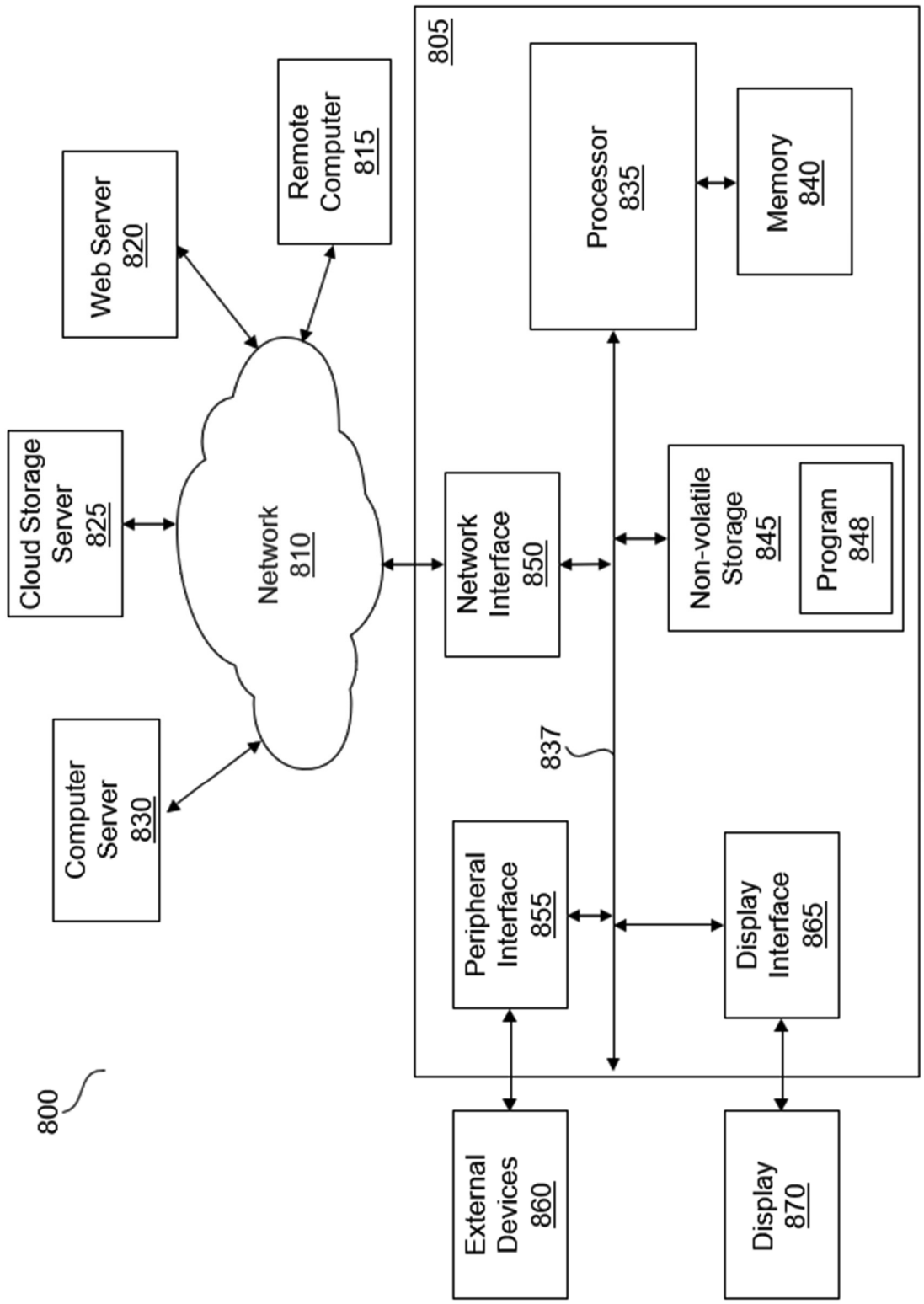

800
805
Web Server 820
Remote Computer 815
Cloud Storage Server 825
Network 810
Computer Server 830
Processor 835
Memory 840
Network Interface 850
Non-volatile Storage 845
Program 848
837
Peripheral Interface 855
Display Interface 865
External Devices 860
Display 870

FIG. 12